

## Facile Liquid-Phase Exfoliated 2D GeP nanosheets for UV-Vis photodetector

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**Table S1.** The light powder density ( $P_\lambda$ ) of the incident light with various irradiation wavelengths. The gradually increased  $P_\lambda$  were labelled with **I**, **II**, **III**, **IV**, and **VI** levels, respectively.

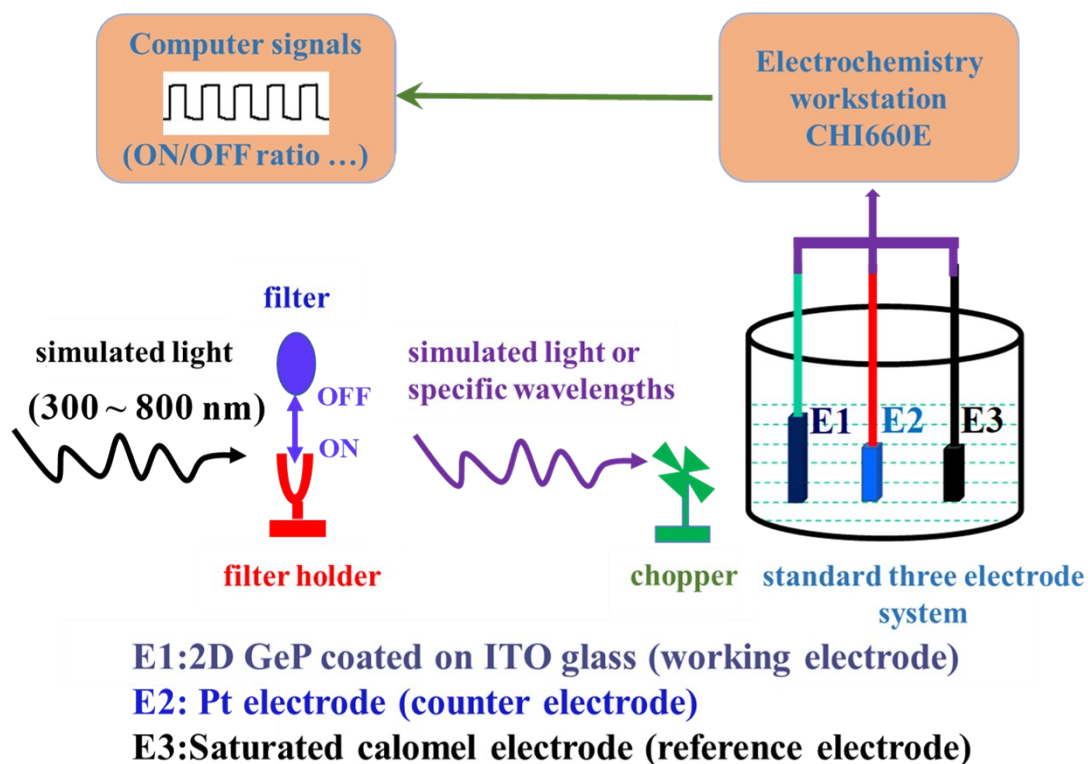
$P_\lambda$ (mW/cm <sup>2</sup> )	I level	II level	III level	IV level	VI level
Simulated light (SL)	26.2	53.0	83.1	118	122
350 nm	0.61	1.52	2.52	3.26	3.41
365 nm	0.76	1.66	2.55	3.57	3.69
380 nm	0.32	1.02	1.91	2.68	2.77
400 nm	0.64	2.04	3.57	5.22	5.35
475 nm	1.91	4.33	7.01	10.1	10.6
550 nm	2.04	3.95	5.98	8.28	8.40
650 nm	2.04	4.08	6.02	8.54	8.92

**Table S2.** Typical parameters of 2D GeP nanosheets-based photodetector at 0.6 V applied bias potential and under 0.5 M KOH electrolyte.

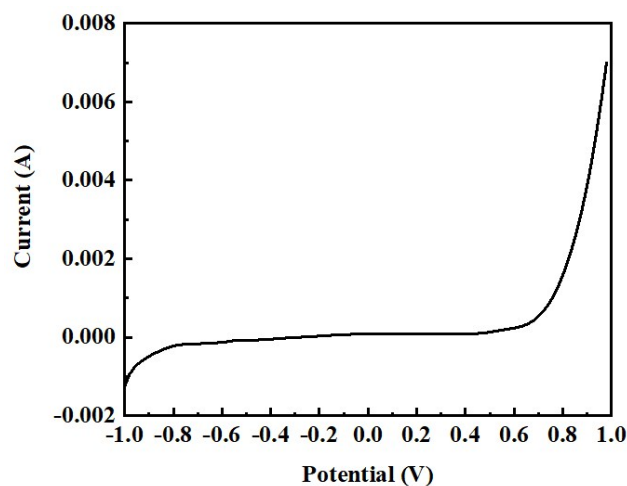
Wavelength (nm)	Light intensity ( $P_{\lambda}$ , $\text{mW}\cdot\text{cm}^{-2}$ )	Responsivity ( $R_{\text{ph}}$ , $\mu\text{A}\cdot\text{W}^{-1}$ )	Detectivity ( $D^*$ , Jones)	EQE (%)
	26.2	12.2	$1.84 \times 10^5$	-
	53.0	10.0	$1.51 \times 10^5$	-
SL	83.1	7.7	$1.16 \times 10^5$	-
	118	6.1	$9.20 \times 10^4$	-
	122	6.3	$9.50 \times 10^4$	-
350	0.61	82.0	$7.89 \times 10^{11}$	29.1
365	0.76	92.1	$1.00 \times 10^{12}$	31.3
380	0.32	187.5	$2.14 \times 10^{12}$	61.3
400	0.64	93.8	$1.11 \times 10^{12}$	29.2
475	1.91	31.4	$3.68 \times 10^{11}$	8.2
550	2.04	9.8	$1.21 \times 10^{11}$	2.2
650	2.04	8.3	$1.04 \times 10^{11}$	1.6

**Table S3.** Comparison of the characteristic parameters of the 2D GeP nanosheets-based photodetector with other reported photodetectors.

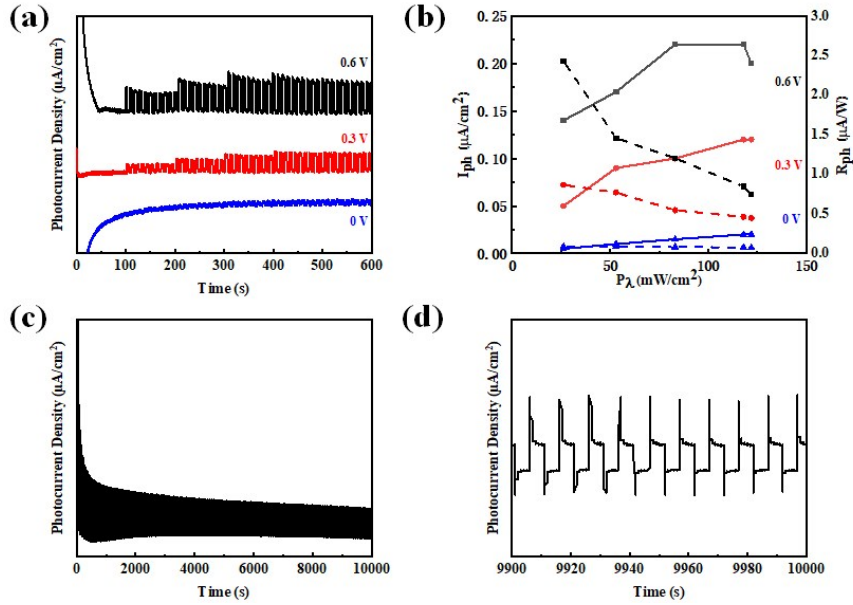
Materials	Device configuration	Measure conditions	Responsivity ( $\mu\text{A W}^{-1}$ )	Detectivity (Jones)	Response time ( $\tau_r/\tau_f$ )	Ref.
2D GeP	PEC	0.5 M KOH, 0.6 V, SL	9.54	$1.84 \times 10^5$	$\sim 0.1/1$ s	This work
2D GeP	PEC	0.5 M KOH, 0.6 V, 380 nm	187.5	$2.14 \times 10^{12}$	$\sim 0.1/1$ s	This work
BP	PEC	0.1 M KOH, 0 V	1.9–2.2	-	0.5/1.1 s	1
InSe	PEC	0.2 M KOH, 1 V	3.3	-	5 s	2
Te	PEC	0.1 M KOH, 0.6 V	1.0–1.3	-	70 ms	3
Bi	PEC	1 M KOH, 0.5 V	1.8	-	2/3 s	4
BP	Photodiode	FET, $V_{ds} = 0.3$ V, $V_g = 0$ V	$4.8 \times 10^3$	-	1 ms	5
GO	Photodiode	FET, $V_{ds} = 1$ V	$2.36 \times 10^4$	$3.31 \times 10^7$	100/105 ms	6
GQDs	Photoconductor	5 V, 254 nm	$2.1 \times 10^3$	$9.59 \times 10^{11}$	64/43 ms	7
ZnO nanocrystals	Photoconductor	120 V, 370 nm	$6.1 \times 10^6$	-	$<0.1/1$ s	8
TiO <sub>2</sub>	Photoconductor	-5 V	$2.1 \times 10^7$	$1.71 \times 10^{12}$	33.4/ >60 s	9
TiO <sub>2</sub> NTs	Photoconductor	0.5 V, 312 nm	$1.3 \times 10^7$	-	0.5/ 0.7 s	10



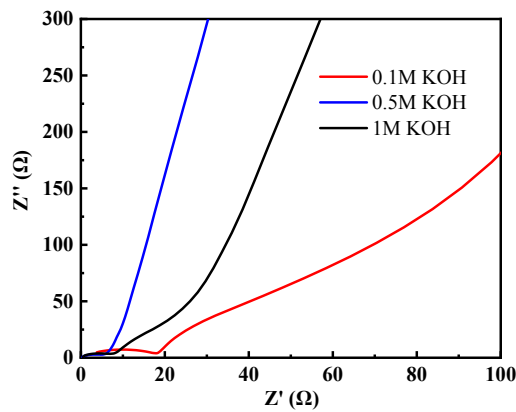
**Scheme S1.** A typical PEC system built for evaluating the photoresponse behavior of the 2D GeP-based photodetectors in different electrolytes.



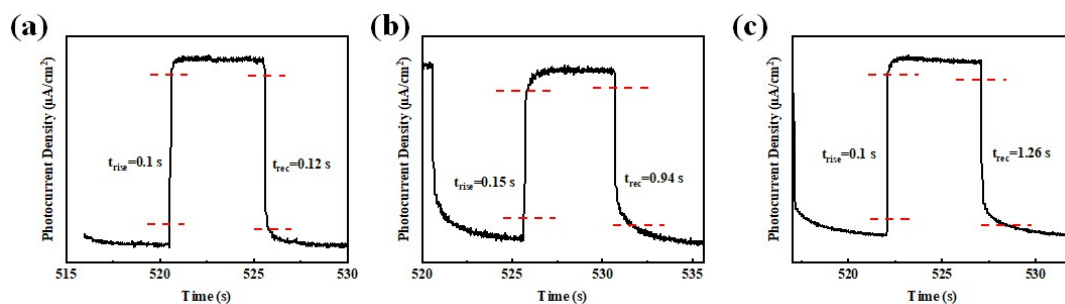
**Figure S1.** Linear sweep voltammetry curves of 2D GeP nanosheets-based photodetectors in 0.5 M KOH.



**Figure S2.** Typical photo-response behavior of the 2D GeP nanosheets-based photodetector in 0.5 M KCl under SL and irradiation with various wavelengths. (a) ON/OFF switching behavior triggered by SL with three selected applied potentials 0, 0.3 and 0.6 V; (b) Calculated photocurrent density (solid lines) and responsivity (dash lines) from (a); (c) Stability of photo-response behaviours of 2D GeP nanosheets-based photodetector with 10000 s cycles with 0.5 M KCl and at voltages of 0.6 V; (d) Enlarged last 100 s cycles of (c).



**Figure S3.** The impedance spectroscopic plots of 2D GeP nanosheets in different KOH electrolyte concentrations (0.1 M, 0.5 M, 1 M).



**Figure S4.** The photocurrent density versus time for the response ( $t_{\text{res}}$ ) and recovery ( $t_{\text{rec}}$ ) times of 2D GeP nanosheets in different KOH electrolyte concentrations (a) 0.1 M, (b) 0.5 M and (c) 1 M.

### Notes and references:

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